**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) plastic package intended for use in general purpose bidirectional switching and phase control applications.

### 2. Features and benefits

- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- · Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Isolated package

### 3. Applications

- General purpose motor control
- · General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
$V_{DRM}$	repetitive peak off-state voltage		6	000		V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 73 °C; Fig. 1; Fig. 2; Fig. 3	8		А	
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	65		А	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	8	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	30	70	mA

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		<b>N</b>
3	G	gate		T2 T1
mb	n.c.	mounting base; isolated		sym051

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BT137X-600F	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

## 7. Marking

### Table 4. Marking codes

Type number	Marking codes
BT137X-600F	BT137X-600F

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# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 73 °C; Fig 1; Fig 2; Fig 3	8	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig 4; Fig 5	65	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	71	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	21	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 50 mA; T2+ G+	50	A/µs
		I <sub>G</sub> = 50 mA; T2+ G-	50	A/µs
		I <sub>G</sub> = 50 mA; T2- G-	50	A/µs
		I <sub>G</sub> = 140 mA; T2- G+	140	A/µs
I <sub>GM</sub>	peak gate current		2	А
$P_{GM}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		125	°C

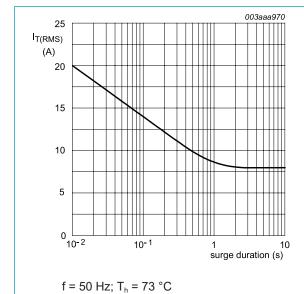


Fig. 1. RMS on-state current as a function of surge duration; maximum values

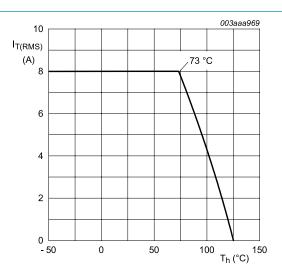
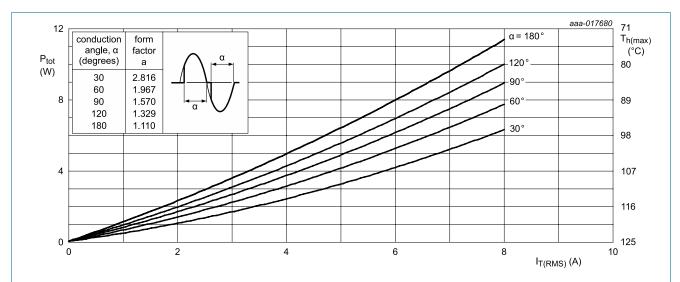


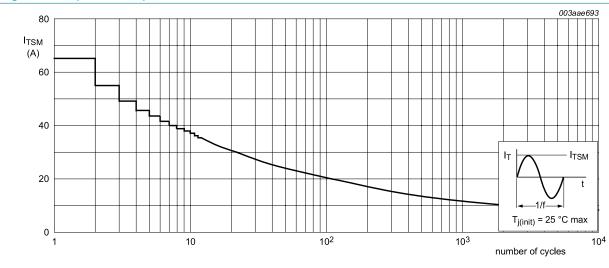
Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



 $\alpha$  = conduction angle

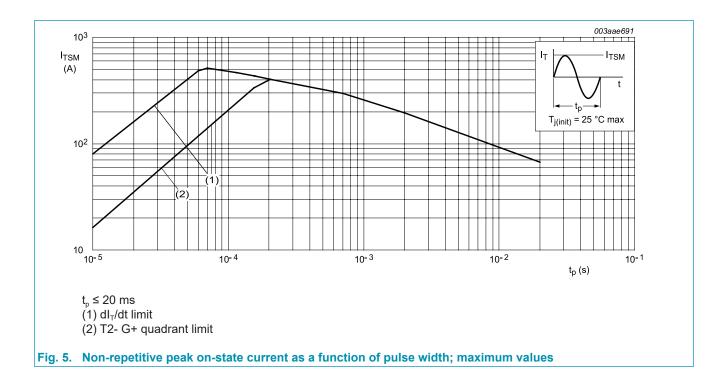
 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

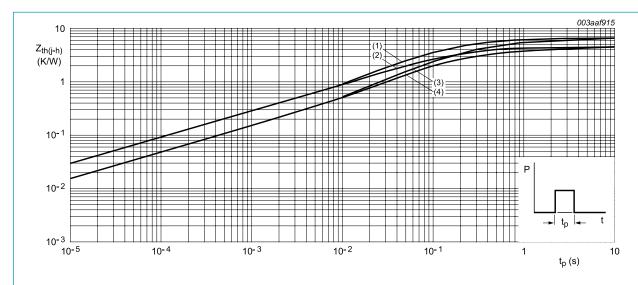


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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig 6	-	-	4.5	K/W
	heatsink	full or half cycle; without heatsink compound; Fig 6	-	-	6.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

### 10. Isolation characteristics

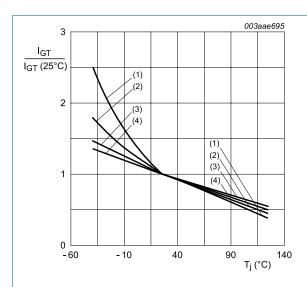
**Table 7. Isolation characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; $T_h = 25$ °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

### 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics			'		
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	8	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	30	70	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	5	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	45	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	5	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V <sub>GT</sub> gate	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	50	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 \text{ °C}; dI_{com}/dt = 3.6 \text{ A/} $ ms; $I_T = 8 \text{ A}$	-	20	-	V/µs
<b>t</b> <sub>gt</sub>	gate-controlled turn-on time	$V_D = 600 \text{ V}; I_{TM} = 12 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

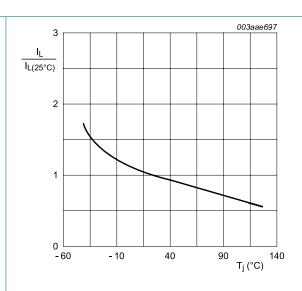


Fig. 8. Normalized latching current as a function of junction temperature

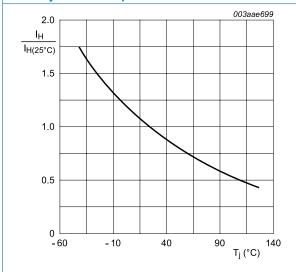
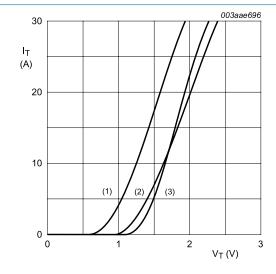


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 1.264 \text{ V}; R_s = 0.038 \Omega$ 

- (1) T<sub>i</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3)  $T_i = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

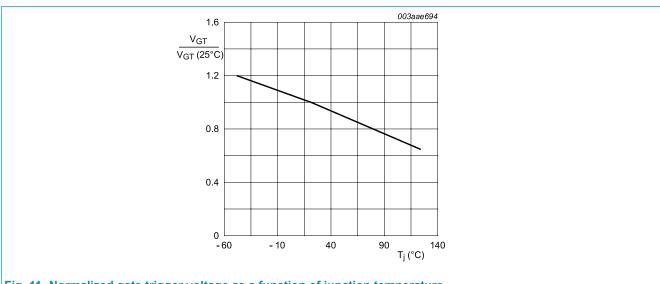
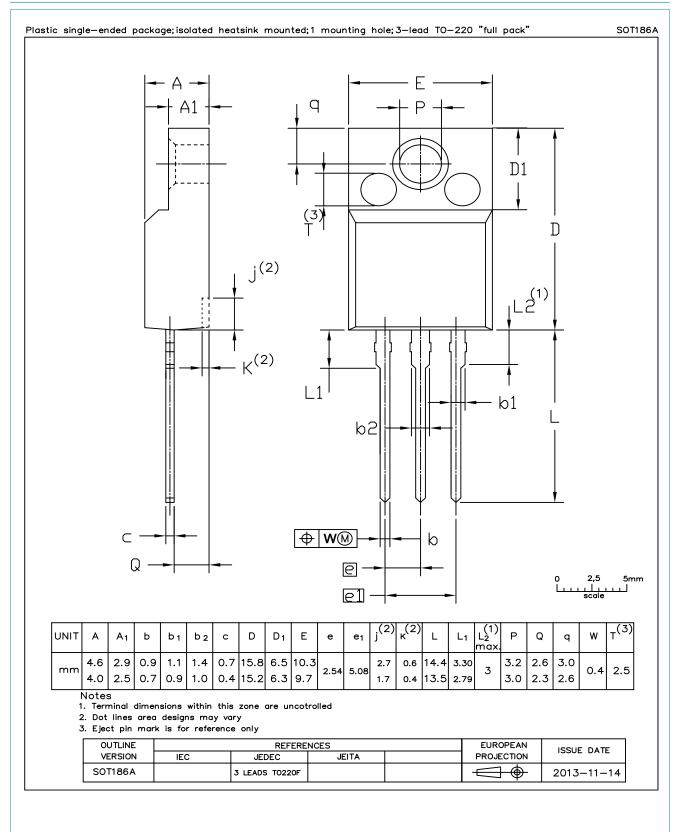


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

## 12. Package outline



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### 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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